Technical Data
TRANSISTOR

DISCRETE SEMICONDUCTOR INDUSTRIES

maximum ratings

Voltage, Collector to Base (VCBO)	140.0	V
Voltage, Collector to Emitter (VCE)	120.0	V
Voltage, Emitter to Base (VEBO)	5.0	V
Collector Current (IC)	16.0	A
Base Current (IB)	0.25	A
Max. Power Dissipation (PT) at TC = 25 °C	150.0	W
Max. Thermal Resistance (Rth J-C)	1.17	°C/W
Max. Junction Temperature (TJ)	200.0	°C

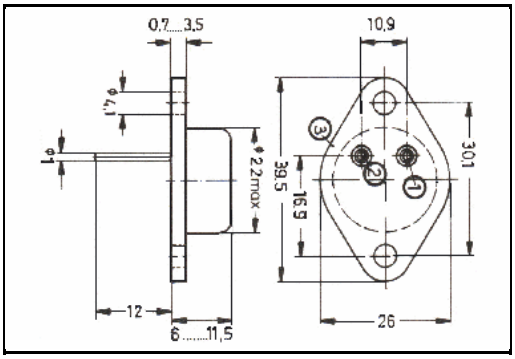
NO.	BDX67C
TYPE	NPN-DARLINGTON
CASE	TO-3

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS		MIN.	MAX.	UNITS
1.	BVCEO	IC = 100.0 mA	(1)	120.0	-	V
2.	ICBO	VCB = 120.0 V		-	1.0	mA
3.	ICBO	VCB = 120.0 V, TJ = 200.0° C		-	5.0	mA
4.	ICEO	VCE = 60.0 V		-	3.0	mA
5.	IEBO	VEB = 5.0 V		-	5.0	mA
6.	hFE	IC = 10.0 A, VCE = 3.0 V	(1)	1k	-	-
7.	hFE	IC = 16.0 A, VCE = 3.0 V	(2)	750.0	-	-
8.	VCE(SAT)	IC = 10.0 A, IB = 40.0 mA	(1)	-	2.0	V
9.	VBE(ON)	IC = 10.0 A, VCE = 3.0 V	(1)	-	2.5	V
10.	fT	IC = 5.0 A, VCE = 3.0 V	(3)	7.0	-	MHz
11.	Cobo	VCB = 10.0 V, f = 1.0 MHz	(3)	-	300.0	pF
12.	VFD	IF = 10.0 A	(3)	-	2.5	V
13.						
14.						
15.						
16.						
17.						
18.						
19.						
20.						

Notes
(1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %
(2)typ. value / pulse-tested tp≤300µs, duty cycle ≤2%
(3)typical value

DIMENSIONS in mm



Marking BDX67C
Customer GENERAL PURPOSE